CTA2N1P

COMPLEX TRANSISTOR ARRAY

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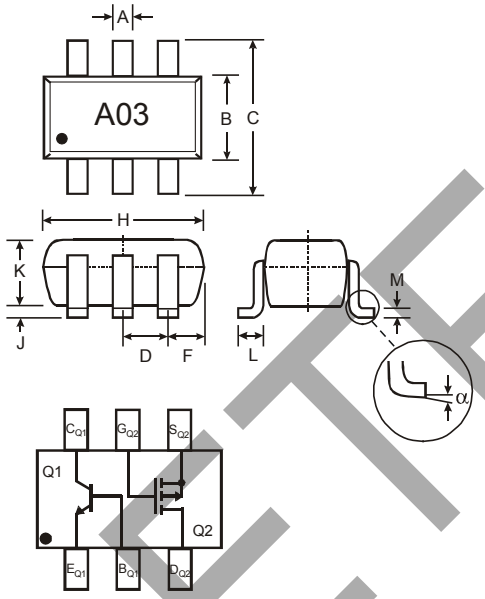
Features

- Combines MMBT4401 type transistor with BSS84 type MOSFET
- Small Surface Mount Package
- PNP/N-Channel Complement Available: CTA2P1N
- **Lead Free/RoHS Compliant (Note 2)**
- **"Green" Device (Note 3 and 4)**

Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Terminal Connections: See Diagram
- Marking Information: A03, See Page 6
- Ordering Information: See Page 6
- Weight: 0.006 grams (approximate)



SOT-363		
Dim	**Min**	**Max**
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
α	0°	8°
All Dimensions in mm		

Maximum Ratings, Total Device @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 1)	P_d	150	mW
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{\theta JA}$	833	°C/W
Operating and Storage Temperature Range		T_j, T_{STG}	-55 to +150	°C

Maximum Ratings, Q1, MMBT4401 NPN Transistor Element @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6.0	V
Collector Current - Continuous	I_C	600	mA

Maximum Ratings, Q2, BSS84 P-Channel MOSFET Element @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$		V_{DGR}	-50	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current	Continuous	I_D	-130	mA

Notes:
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
2. No purposefully added lead.
3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
4. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

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Electrical Characteristics, Q1, MMBT4401 NPN Transistor Element @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	60	—	V	I_C = 100μA, I_E = 0
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	40	—	V	I_C = 1.0mA, I_B = 0
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	6.0	—	V	I_E = 100μA, I_C = 0
Collector Cutoff Current	I_{CEX}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
Base Cutoff Current	I_{BL}	—	100	nA	V_{CE} = 35V, $V_{EB(OFF)}$ = 0.4V
ON CHARACTERISTICS (Note 5)					
DC Current Gain	h_{FE}	20 40 80 100 40	— — — 300 —	—	I_C = 100μA, V_{CE} = 1.0V I_C = 1.0mA, V_{CE} = 1.0V I_C = 10mA, V_{CE} = 1.0V I_C = 150mA, V_{CE} = 1.0V I_C = 500mA, V_{CE} = 2.0V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	0.40 0.75	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	0.75 —	0.95 1.2	V	I_C = 150mA, I_B = 15mA I_C = 500mA, I_B = 50mA
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	6.5	pF	V_{CB} = 5.0V, f = 1.0MHz, I_E = 0
Input Capacitance	C_{eb}	—	30	pF	V_{EB} = 0.5V, f = 1.0MHz, I_C = 0
Input Impedance	h_{ie}	1.0	15	kΩ	V_{CE} = 10V, I_C = 1.0mA, f = 1.0kHz
Voltage Feedback Ratio	h_{re}	0.1	8.0	x 10^{-4}	
Small Signal Current Gain	h_{fe}	40	500	—	
Output Admittance	h_{oe}	1.0	30	μS	
Current Gain-Bandwidth Product	f_T	250	—	MHz	V_{CE} = 10V, I_C = 20mA, f = 100MHz
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	V_{CC} = 30V, I_C = 150mA, $V_{BE(off)}$ = 2.0V, I_{B1} = 15mA
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	V_{CC} = 30V, I_C = 150mA, I_{B1} = I_{B2} = 15mA
Fall Time	t_f	—	30	ns	

Electrical Characteristics, Q2, BSS84 P-Channel MOSFET Element @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV_{DSS}	-50	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current	I_{DSS}	— — —	— — —	-15 -60 -100	μA μA nA	V_{DS} = -50V, V_{GS} = 0V, T_J = 25°C V_{DS} = -50V, V_{GS} = 0V, T_J = 125°C V_{DS} = -25V, V_{GS} = 0V, T_J = 25°C
Gate-Body Leakage	I_{GSS}	—	—	±10	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	$V_{GS(th)}$	-0.8	—	-2.0	V	V_{DS} = V_{GS}, I_D = -1mA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	—	10	Ω	V_{GS} = -5V, I_D = 0.100A
Forward Transconductance	g_{FS}	.05	—	—	S	V_{DS} = -25V, I_D = 0.1A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C_{iss}	—	—	45	pF	V_{DS} = -25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance	C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C_{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{D(ON)}$	—	10	—	ns	V_{DD} = -30V, I_D = -0.27A, R_{GEN} = 50Ω, V_{GS} = -10V
Turn-Off Delay Time	$t_{D(OFF)}$	—	18	—	ns	

Notes: 5. Short duration pulse test used to minimize self-heating effect.

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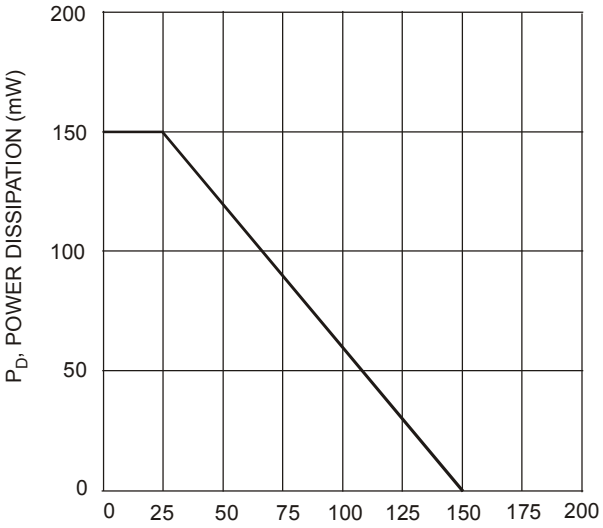

Fig. 1 Max Power Dissipation vs. Ambient Temperature (Total Device)

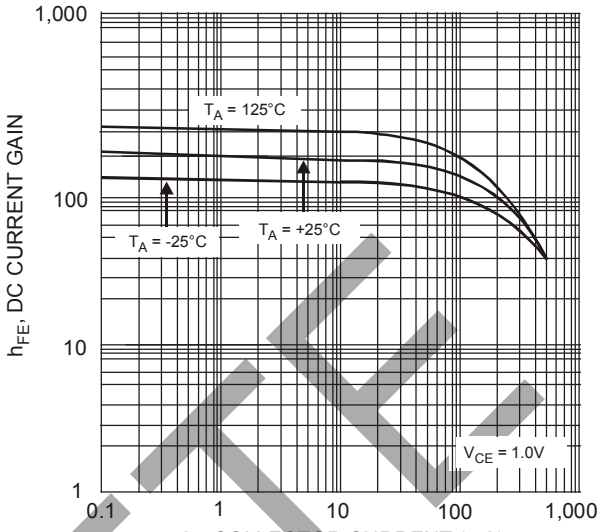

Fig. 2 Typical DC Current Gain vs. Collector Current

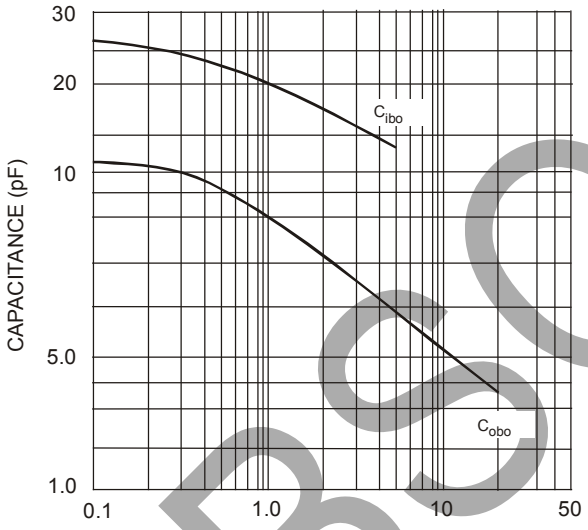

Fig. 3 Typical Capacitance

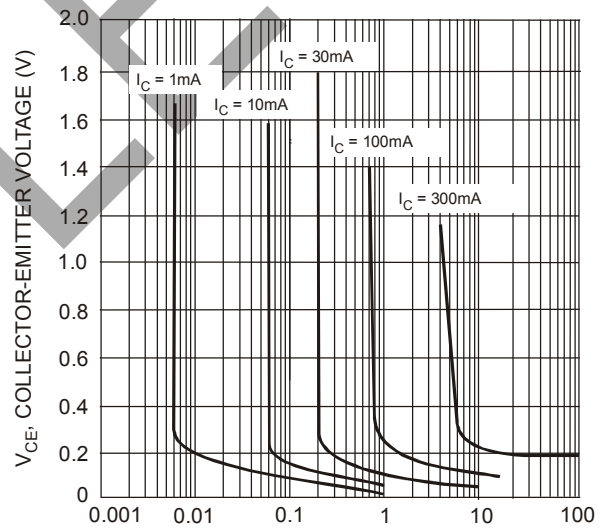

Fig. 4 Typical Collector Saturation Region

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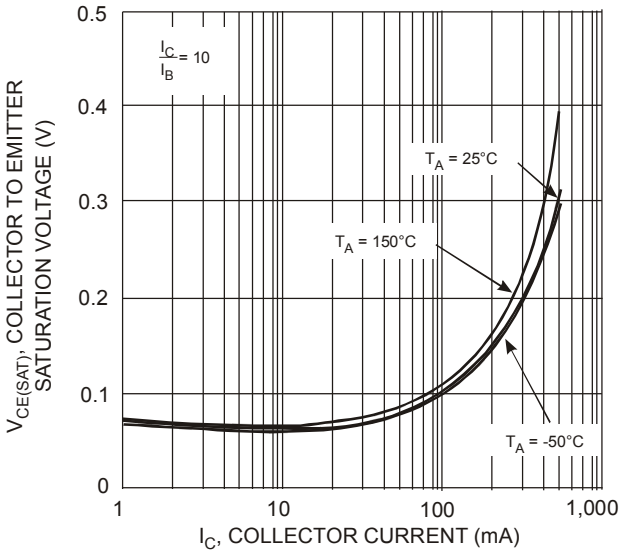

Fig. 5 Collector Emitter Saturation Voltage vs. Collector Current

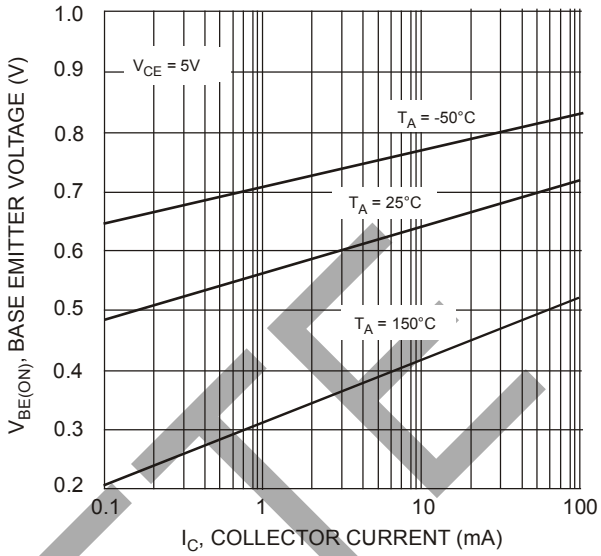

Fig. 6 Base Emitter Voltage vs. Collector Current

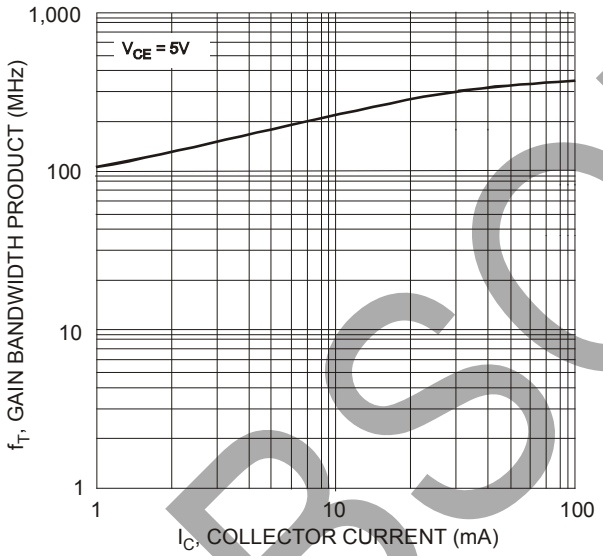

Fig. 7 Gain Bandwidth Product vs. Collector Current

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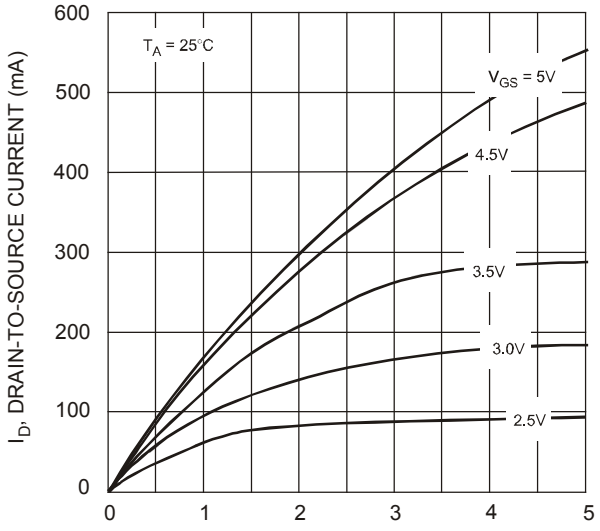

Fig. 8 Drain-Source Current vs. Drain-Source Voltage

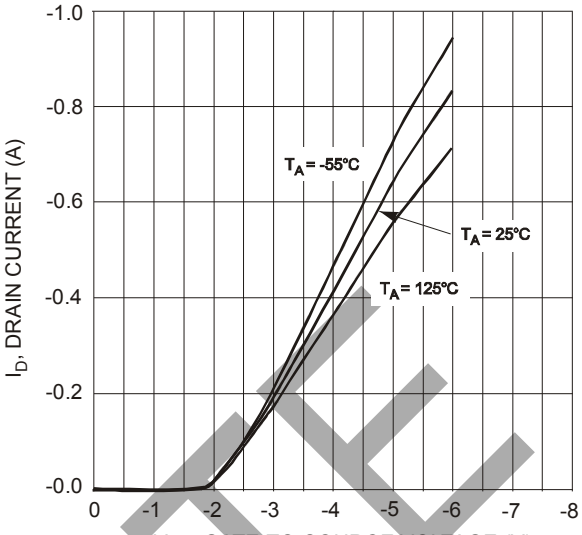

Fig. 9 Drain Current vs. Gate Source Voltage

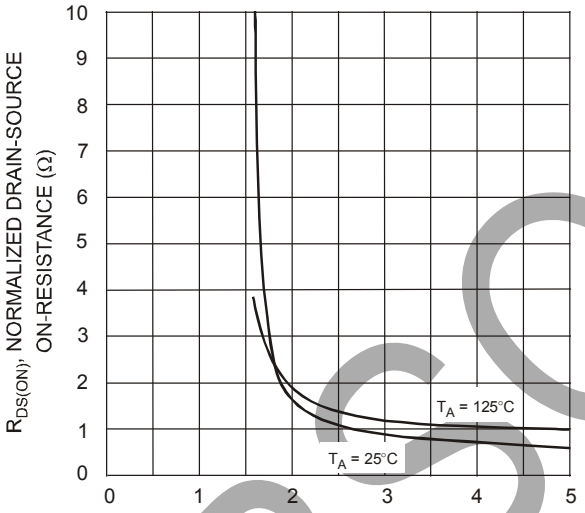

Fig. 10 On-Resistance vs. Gate-Source Voltage

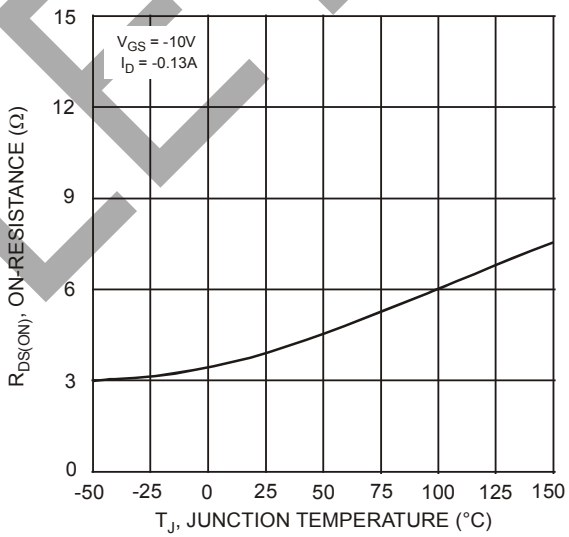

Fig. 11 On-Resistance vs. Junction Temperature

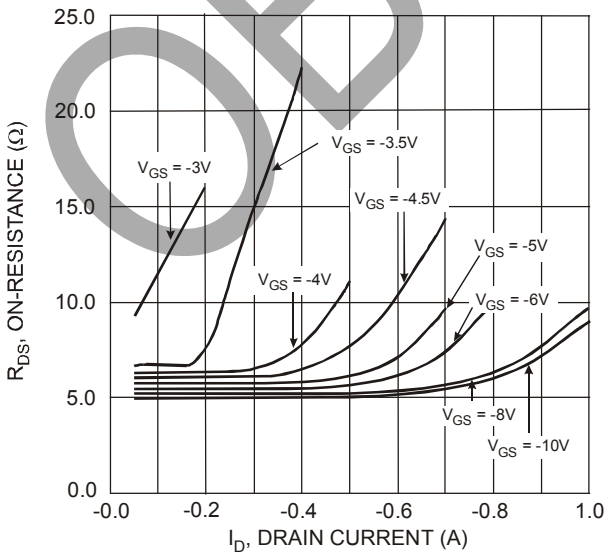

Fig. 12, On-Resistance vs. Drain Current

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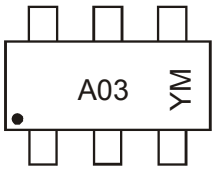
Ordering Information (Note 6)

Device	Packaging	Shipping
CTA2N1P-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



A03 = Product Type Marking Code
YM = Date Code Marking
Y = Year ex: T = 2006
M = Month ex: 9 = September

Date Code Key

Year	2001	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	M	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

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